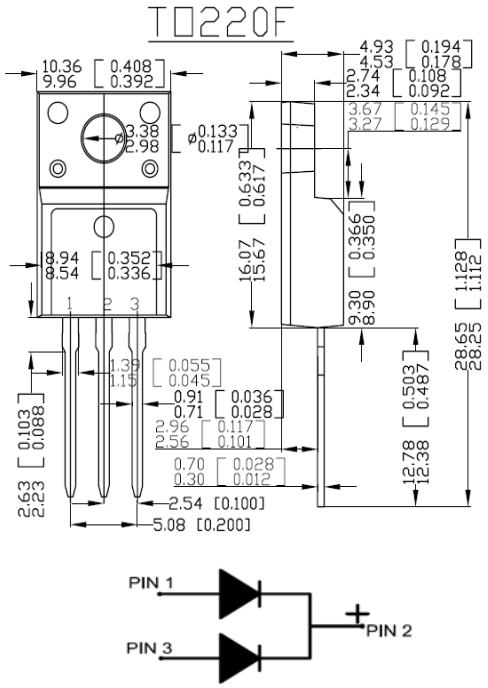
SHENZHEN HAOLIN ELECTRONICS TECHNOLOGY CO., LTD

TO- 220F SCHOTTKY BARRIER RECTIFIERS

MBR20150CT



Dimensions in millimeters and (inches)

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss,High Effciency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage,High Frequency Inverters,Free Wheeling,and Polarity Protection Applications

ELECTRICAL CHARACTERISTICS (Tamb=25^{0}C)

Characteristic	Symbol	MBR20150CT	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	150	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectifide Output Current	I_C	20	A
Maximum Instaneous Forward Voltage			
@I_F =10A,Tc=25 ^{0}C	V_F	0.85	V
@I_F =10A,Tc=125 ^{0}C		0.82	
@I_F =20A,Tc=25 ^{0}C		0.95	
@I_F =20A,Tc=125 ^{0}C		0.85	
Peak Reverse Current @Tc=25 ^{0}C	I_R	50	uA
at Rated DC Blocking Voltage @Tc=125 ^{0}C		200	
Operating and Storage Temperature Range	T_j ,T_{stg}	-55 to +150	^{0}C

Fig. 1: Average forward power dissipation versus average forward current (per diode).

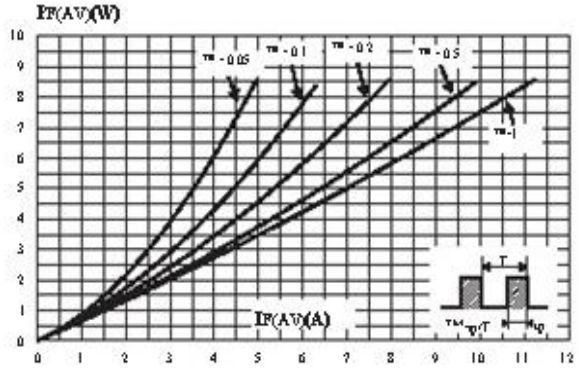


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

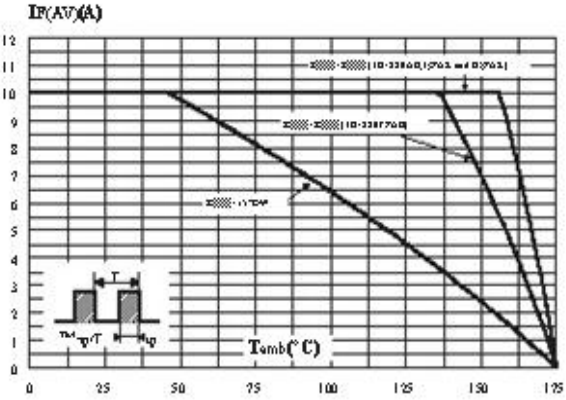


Fig. 3: Junction capacitance versus reverse voltage applied (typical values, per diode).

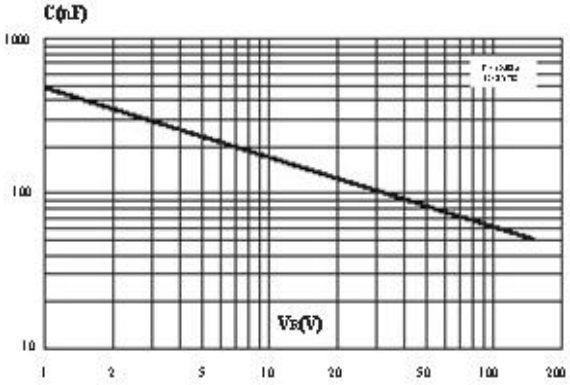


Fig. 4: Normalized avalanche power derating versus junction temperature.

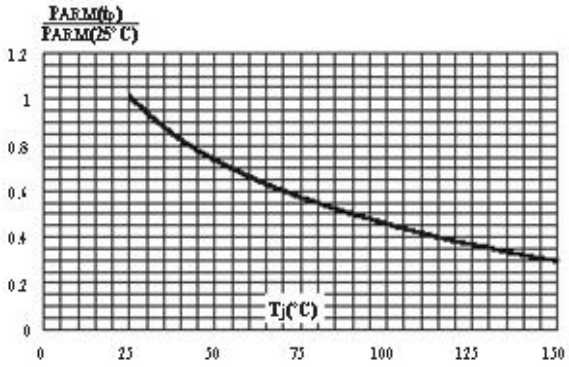


Fig.5 : Reverse leakage current versus reverse voltage applied (typical values, per diode).

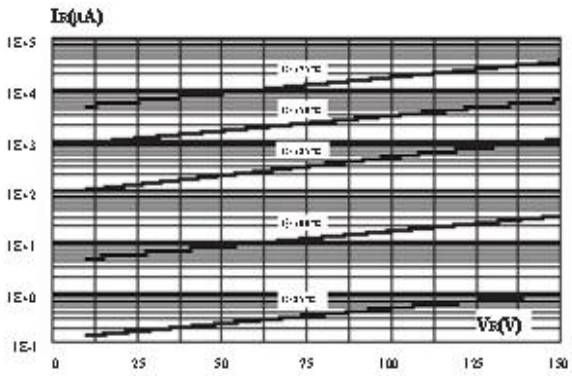


Fig. 6: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).